

# BCR12PM-12LC

# Triac

Medium Power Use

REJ03G1261-0300 Rev.3.00 Dec 20, 2006

#### **Features**

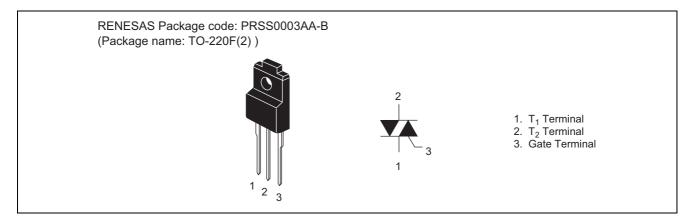
I<sub>T (RMS)</sub>: 12 A
 V<sub>DRM</sub>: 600 V

 $\bullet \quad I_{FGTI},\,I_{RGTI},\,I_{RGTIII}:50\;mA$ 

• Viso: 1500 V

- The product guaranteed maximum junction temperature 150°C.
- Insulated Type
- Planar Passivation Type

## **Outline**



## **Applications**

Heater control, motor control

# **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	600	V
Non-repetitive peak off-state voltage Note1	V <sub>DSM</sub>	700	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T (RMS)</sub>	12	Α	Commercial frequency, sine full wave 360° conduction, Tc = 77°C
Surge on-state current	I <sub>TSM</sub>	72	А	60Hz sinewave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	21.6	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P <sub>GM</sub>	5	W	
Average gate power dissipation	P <sub>G (AV)</sub>	0.5	W	
Peak gate voltage	$V_{GM}$	10	V	
Peak gate current	I <sub>GM</sub>	2	Α	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	_	2.0	g	Typical value
Isolation voltage	Viso	1500	V	Ta = 25°C, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

## **Electrical Characteristics**

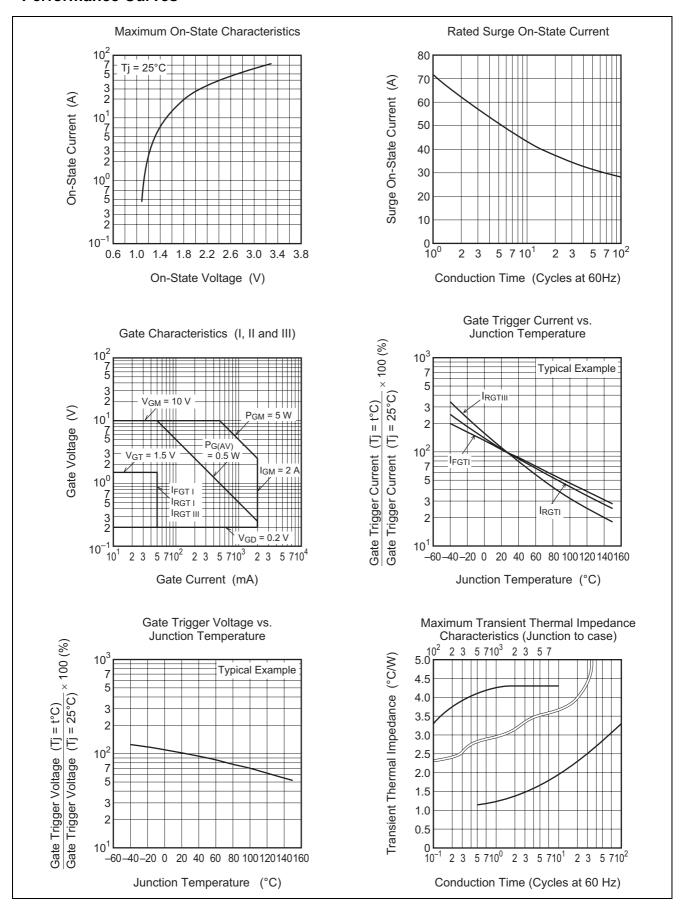
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I <sub>DRM</sub>	_	_	2.0	mA	Tj = 125°C, V <sub>DRM</sub> applied
On-state voltage		$V_{TM}$	_	_	1.8	V	Tc = 25°C, I <sub>TM</sub> = 20 A, Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGT_{\mathrm{I}}}$	_	_	1.5	V	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ $\Omega$ ,
	II	$V_{RGT_I}$	_	_	1.5	V	$R_G = 330 \Omega$
	III	$V_{RGT_{III}}$	_	_	1.5	V	
Gate trigger current <sup>Note2</sup>		I <sub>FGTI</sub>	_	_	50	mA	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega$
	II	$I_{RGT_{\mathrm{I}}}$	_	_	50	mA	$R_G = 330 \Omega$
	III	I <sub>RGTIII</sub>	_	_	50	mA	
Gate non-trigger voltage	•	$V_{GD}$	0.2	_	_	V	$Tj = 125$ °C, $V_D = 1/2 V_{DRM}$
Thermal resistance		R <sub>th (j-c)</sub>	_	_	4.3	°C/W	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutating voltage <sup>Note4</sup>		(dv/dt)c	10	_	_	V/μs	Tj = 125°C

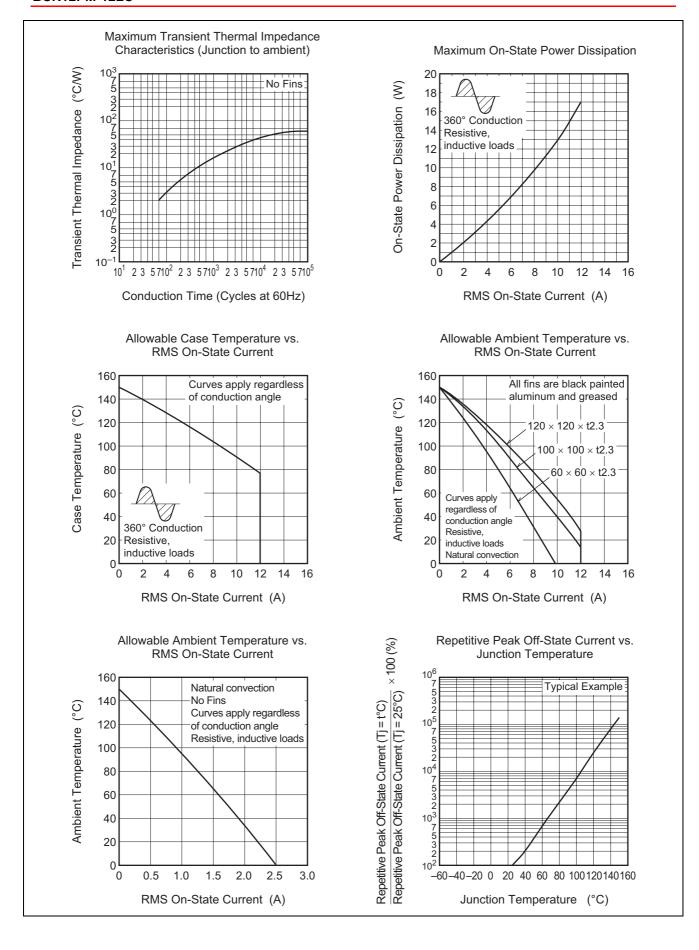
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

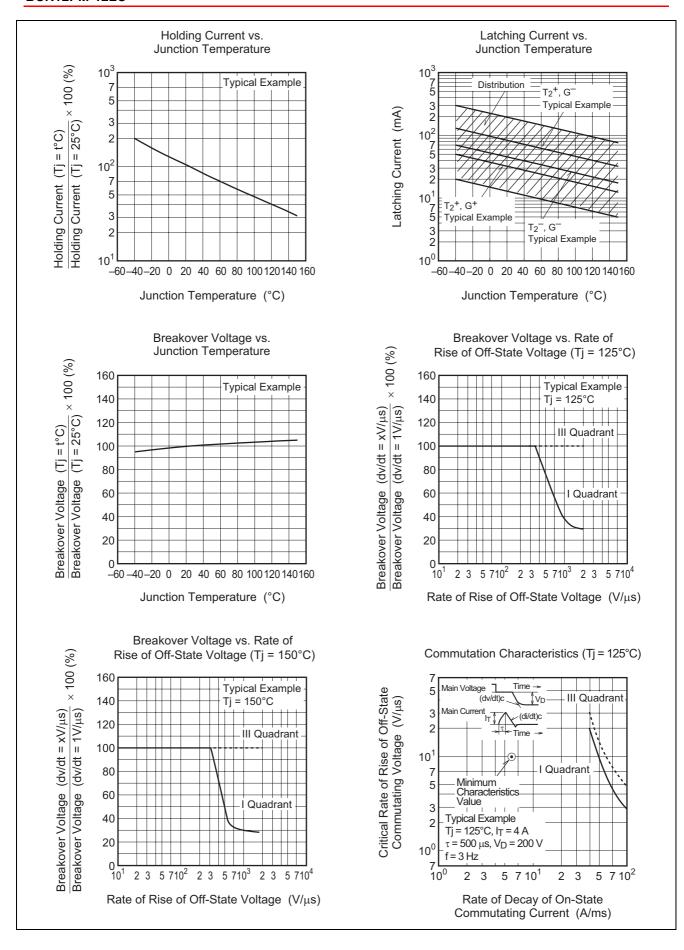
- 3. The contact thermal resistance  $R_{th\ (c\text{-}f)}$  in case of greasing is 0.5°C/W.
- 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

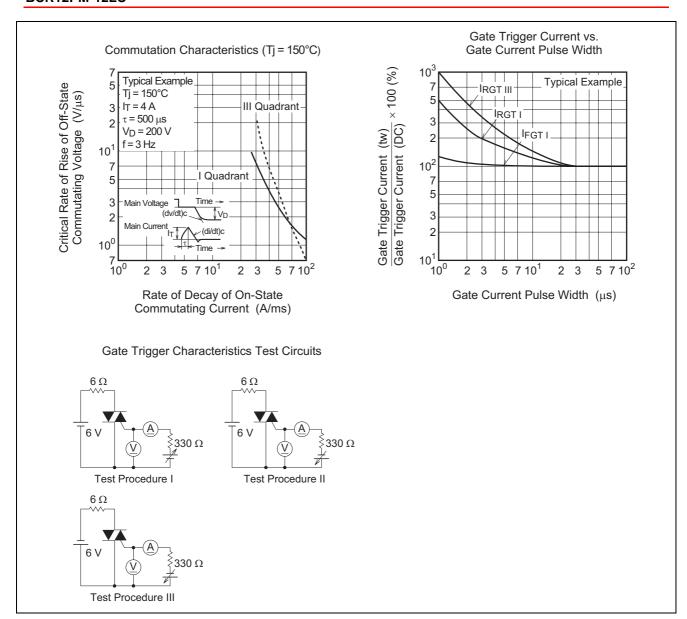
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C	Supply Voltage  → Time
2. Rate of decay of on-state commutating current (di/dt)c = - 6 A/ms	Main Current (di/dt)c → Time
3. Peak off-state voltage $V_D = 400 \text{ V}$	Main Voltage Time

## **Performance Curves**

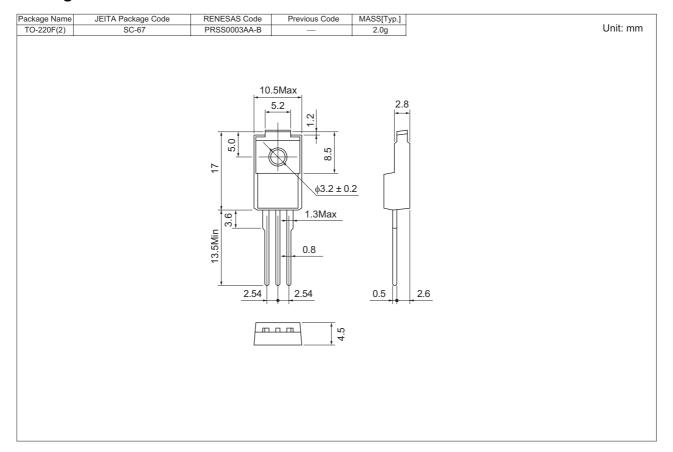








# **Package Dimensions**



## **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR12PM-12LC
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR12PM-12LC-A8

Note: Please confirm the specification about the shipping in detail.

#### Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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**Renesas Technology America, Inc.** 450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd. 1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

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